

100V N-Channel MOSFET

100 V

Voltage

Features

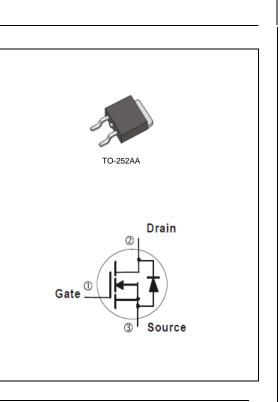
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@4.5A < 152m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V,I_D@3.0A<158mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.

Current

• Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: TO-252AA Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25[°]C unless otherwise noted)

9 A

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	9	A	
	T _C =100°C		6		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	18		
Power Dissipation	T _C =25°C	PD	31	W	
	T _C =100°C		12		
Continuous Drain Current	T _A =25°C	I _D	2.4	А	
	T _A =70°C		1.9	А	
Power Dissipation	T _A =25°C	5	2.0	W	
Power Dissipation	T _A =70°C	Po	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	1.8	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ extsf{ heta}JC}$	4.0	°C/W	
	Junction to Ambient	R_{\thetaJA}	62.5		

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

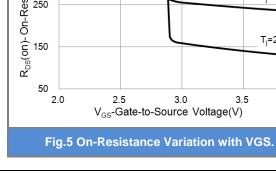
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.72	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =4.5A	-	130	152	mΩ
		V _{GS} =4.5V,I _D =3A	-	135	158	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 4)		·				
Total Gate Charge	Qg	V _{DS} =60V, I _D =9A, V _{GS} =10V ^(Note 2,3)	-	19	-	nC
Gate-Source Charge	Q _{gs}		-	2.9	-	
Gate-Drain Charge	Q _{gd}		-	3.2	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1021	-	pF
Output Capacitance	Coss		-	38	-	
Reverse Transfer Capacitance	Crss		-	17	-	
Turn-On Delay Time	td _(on)		-	6.1	-	ns
Turn-On Rise Time	t _r	V _{DS} =50V,RL=5.6Ω, V _{GS} =10V, R _G =6Ω (Note 2.3)	-	27	-	
Turn-Off Delay Time	td _(off)		-	28	-	
Turn-Off Fall Time	t _f	(-	11	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	9	A
Diode Forward Current	I _S					
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.74	1.2	V

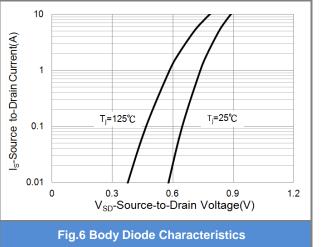
NOTES:

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, $I_{AS}{=}6A,\,V_{DD}{=}25V,\,V_{GS}{=}10V$
- 7. Guaranteed by design, not subject to production testing



PJD9N10A **TYPICAL CHARACTERISTIC CURVES** 12 12 10V,8V,5V V_{DS}=5V I_{DS}-Drain-to-S ource Current(A) $V_{GS}=3V$ I_{DS}-Drain-to-Source Current(A) 9 9 6 6 T_=25℃ T_=125℃ 3 3 V_{GS}=2.5V 0 0 0 3 5 1 2 4 0 5 1 3 4 2 V_{DS}- Drain-to-Source Voltage(V) V_{GS}-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 200 2.5 R_{DS}(on)- On-Resistance (Normalized) V_{GS}=10V, I_D=4.5A $R_{DS}(on)$ - On-Resistance(m Ω) 180 2.0 160 1.5 V_{GS}= 4.5V 140 1.0 120 V_{GS} = 10V 100 0.5 0 2 6 8 0 4 10 12 25 50 75 100 125 150 175 Temperature (°C) IDS-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 450 10 I_D=2.25A R_{DS}(on)- On-Resistance(mΩ) 05 05 05 I_s-Source to-Drain Current(A) 1 Tj=125℃ Tj=125℃ T_i=25℃ 0.1 Tj=25℃ 50 0.01 2.0 2.5 3.0 3.5 4.0 0 0.3 0.6 0.9 1.2 V_{GS}-Gate-to-Source Voltage(V) V_{SD}-Source-to-Drain Voltage(V)







TYPICAL CHARACTERISTIC CURVES

Fig.7 Gate-Charge Characteristics

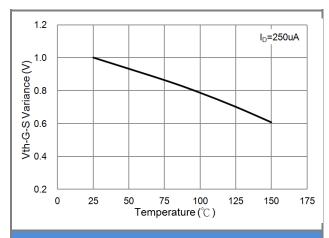
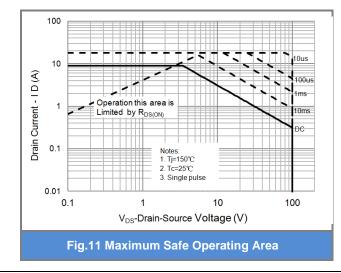
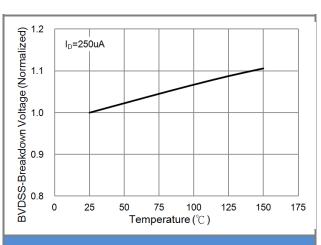


Fig.9 Threshold Voltage Variation with Temperature







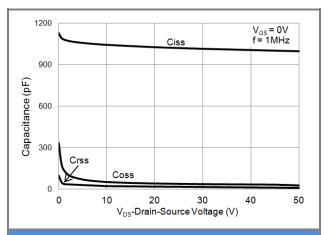
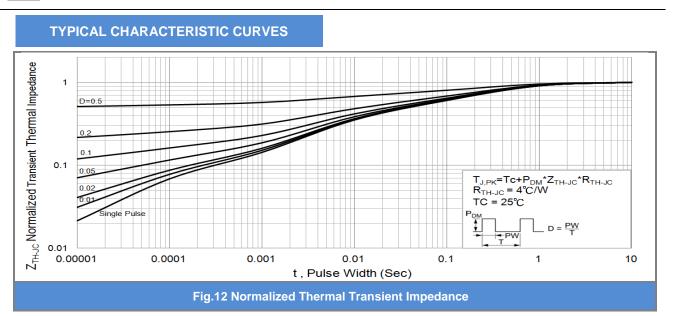


Fig.10 Capacitance vs. Drain-Source Voltage

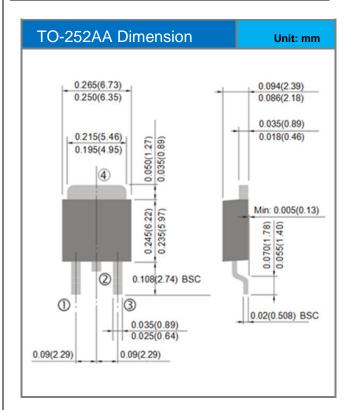








Packaging Information

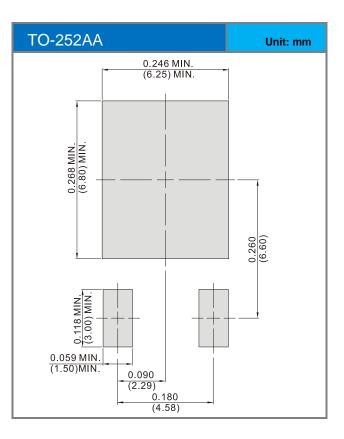




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type Marking		Version	
PJD9N10A_L2_00001	TO-252AA	3,000pcs / 13" reel	D9N10A	Halogen free	

MOUNTING PAD LAYOUT





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